

Table of Contents

Preface, Committees and Sponsors

Chapter I: SiC Material

I.1 Bulk Growth

Dislocation Conversion During SiC Solution Growth for High-Quality Crystals

S. Harada, Y. Yamamoto, S. Xiao, D. Koike, T. Mutoh, K. Murayama, K. Aoyagi, T. Sakai, M. Tagawa and T. Ujihara 3

4H-SiC Growth from Si-Cr-C Solution under Al and N Co-Doping Conditions

T. Mitani, N. Komatsu, T. Takahashi, T. Kato, T. Ujihara, Y. Matsumoto, K. Kurashige and H. Okumura 9

Change in Surface Morphology by Addition of Impurity Elements in 4H-SiC Solution Growth with Si Solvent

N. Komatsu, T. Mitani, T. Takahashi, T. Kato, K. Kurashige, Y. Matsumoto, T. Ujihara and H. Okumura 14

Control of Interface Shape by Non-Axisymmetric Solution Convection in Top-Seeded Solution Growth of SiC Crystal

D. Koike, T. Umezaki, K. Murayama, K. Aoyagi, S. Harada, M. Tagawa, T. Sakai and T. Ujihara 18

Effect of Forced Convection by Crucible Design in Solution Growth of SiC Single Crystal

K. Kurashige, M. Aoshima, K. Takei, K. Fujii, M. Hiratani, N. Senguttuvan, T. Kato, T. Ujihara, Y. Matsumoto and H. Okumura 22

Effects of Crystalline Polarity and Temperature Gradient on Step Bunching Behavior of Off-Axis 4H-SiC Solution Growth

S. Endo, K. Kamei, Y. Kishida and K. Moriguchi 26

Improvement of Surface Morphology by Solution Flow Control in Solution Growth of SiC on Off-Axis Seeds

T. Umezaki, D. Koike, S. Harada and T. Ujihara 31

Influences of Solution Flow and Lateral Temperature Distribution on Surface Morphology in Solution Growth of SiC

K. Fujii, K. Takei, M. Aoshima, N. Senguttuvan, M. Hiratani, T. Ujihara, Y. Matsumoto, T. Kato, K. Kurashige and H. Okumura 35

Research on Solvent Composition for Different Surface Morphology on C Face during 4H-SiC Solution Growth

S. Xiao, N. Hara, S. Harada, K. Murayama, K. Aoyagi, T. Sakai and T. Ujihara 39

Effect of Porous Graphite for High Quality SiC Crystal Growth by PVT Method

H.J. Lee, H.T. Lee, H.W. Shin, M.S. Park, Y.S. Jang, W.J. Lee, I.G. Yeo, T.H. Eun, J.Y. Kim, M.C. Chun, S.H. Lee and J.G. Kim 43

Growth Study of p-Type 4H-SiC with Using Aluminum and Nitrogen Co-Doping by 2-Zone Heating Sublimation Method

K. Eto, T. Kato, S. Takagi, T. Miura, Y. Urakami, H. Kondo, F. Hirose and H. Okumura 47

High Quality 100 mm 4H-SiC Substrate

Y.Q. Gao, H.Y. Zhang, J. Song, S. Song, Q.R. Liang, M. Ning, C. Gao, X.J. Wang, Y.M. Zong, H.H. Wang and M. Dudley 51

High Quality 150 mm 4H SiC Wafers for Power Device Production

J. Quast, D. Hansen, M. Loboda, I. Manning, K. Moeggenborg, S. Mueller, C. Parfeniuk, E. Sanchez and C. Whiteley 56

Nitrogen Incorporation during Seeded Sublimation Growth of 4H-SiC and 6H-SiC

N. Tsavdaris, P. Kwasnicki, K. Ariyawong, N. Valle, H. Peyre, E. Sarigiannidou, S. Juillaguet and D. Chaussende 60

Observation of the Surface Morphology on the (0001)C Facet of 4H-SiC Boules

T. Yamaguchi, S. Sato, N. Ohtani, M. Katsuno, T. Fujimoto, S. Sato, H. Tsuge and T. Yano 64

Physical Vapor Transport Growth of 4H-SiC on {000-1} Vicinal Surfaces

X.L. Yang, K. Yang, X.F. Chen, Y. Peng, X.B. Hu and X.G. Xu 68

Polarity Inversion of SiC(0001) during the Al Doped PVT Growth

K. Eto, T. Miura, T. Kato and H. Okumura 73

Quantitative Study of the Role of Supersaturation during Sublimation Growth on the Yield of 50 mm 3C-SiC	
D. Rankl, V. Jokubavicius, M. Syväjärvi and P.J. Wellmann	77
SIMS Analysis of Fe Impurity Concentration in a PVT-Grown 4H-SiC Bulk Crystal and Source Powders	
N. Iwamoto, A. Azarov, L. Vines, A.M.M. Moe and B.G. Svensson	81
Stacking Fault Formation via 2D Nucleation in PVT Grown 4H-SiC	
F.Z. Wu, H.H. Wang, Y. Yang, J.Q. Guo, B. Raghothamachar, M. Dudley, S.G. Mueller, G.Y. Chung, E. Sanchez, D. Hansen, M.J. Loboda, L.H. Zhang, D. Su, K. Kisslinger and E. Stach	85
Structural and Electrical Characterization of the Initial Stage of Physical Vapor Transport Growth of 4H-SiC Crystals	
T. Takahashi, C. Ohshige, N. Ohtani, M. Katsuno, T. Fujimoto, S. Sato, H. Tsuge, T. Yano, H. Matsuhata and M. Kitabatake	90
Assessment of SiC Crystal Chemistry during the PVT Growth Process: Coupled Numerical Modeling and Thermodynamics Approach	
K. Ariyawong, C. Chatillon, E. Blanquet, J.M. Dedulle and D. Chaussende	96
Characterization of Second-Phase Inclusion in Silicon Carbide Powders	
T.C. Hsiao, S. Tsao, S. Nagalyuk and E. Mokhov	100
High-Speed and Long-Length SiC Growth Using High-Temperature Gas Source Method	
J. Kojima, E. Makino, Y. Tokuda, N. Sugiyama, N. Hoshino and H. Tsuchida	104

I.2 Epitaxial and Thin Film Growth

Controlling Planar Defects in 3C-SiC: Ways to Wake it up as a Practical Semiconductor	
H. Nagasawa, R. Gurunathan and M. Suemitsu	108
Ge Addition during 4H-SiC Epitaxial Growth by CVD: Mechanism of Incorporation	
V. Soulière, K. Alassaad, F. Cauwet, H. Peyre, T. Kups, J. Pezoldt, P. Kwasnicki and G. Ferro	115
Behavior and Chemical Reactions of Liquid Si and Ge on SiC Surface	
K. Alassaad, V. Soulière, F. Cauwet, D. Carole and G. Ferro	121
Cleaning Process for Using Chlorine Trifluoride Gas Silicon Carbide Chemical Vapor Deposition Reactor	
H. Habuka, Y. Fukumoto, K. Mizuno, Y. Ishida and T. Ohno	125
Effect of C/Si Ratio and Nitrogen Doping on 4H-SiC Epitaxial Growth Using Dichlorosilane Precursor	
H.Z. Song, M.V.S. Chandrashekhhar and T.S. Sudarshan	129
Influence of Growth Pressure and Addition of HCl Gas on Growth Rate of 4H-SiC Epitaxy	
T. Tanaka, N. Kawabata, Y. Mitani, M. Sakai, N. Tomita, M. Tarutani, T. Kuroiwa, Y. Toyoda, M. Imaizumi, H. Sumitani and S. Yamakawa	133
Study of SiC Epitaxial Growth Using Tetrafluorosilane and Dichlorosilane in Vertical Hotwall CVD Furnace	
A. Balachandran, H.Z. Song, T.S. Sudarshan, S.S. Shetu and M.V.S. Chandrashekhhar	137
The Role of Chlorine during High Growth Rate Epitaxy	
R. Karhu, I. Booker, J. Hassan, I. Ivanov and E. Janzén	141
Study of Al Incorporation in Chemical Vapor Deposition of p-Doped SiC	
A.S. Segal, S.Y. Karpov, A.V. Lobanova, E. YAKOVLEV, K. Hara and M. Naito	145
Influence of Site Competition Effects on Dopant Incorporation during Chemical Vapor Deposition of 4H-SiC Epitaxial Layers	
R. Arvinte, M. Zielinski, T. Chassagne, M. Portail, A. Michon, P. Kwasnicki, S. Juillaguet and H. Peyre	149
150 mm 4H-SiC Epitaxial Layer Growth in a Warm-Wall Planetary Reactor	
Y.Q. Sun, G. Feng, L.P. Lv, W.N. Qian, Y.Y. Li, J.Y. Luo and J.H. Zhang	153
Epitaxial Growth on 150 mm 2° off Wafers	
F. La Via, N. Piluso, P. Fiorenza, M. Mauceri, C. Vecchio, A. Pecora and D. Crippa	157
Progress of SiC Epitaxy on 150mm Substrates	
J. Zhang, B. Thomas, K. Moeggenborg, V.M. Torres and D. Hansen	161
SiC Epitaxial Growth in a 7x100mm/3x150mm Horizontal Hot-Wall Batch Reactor	
T. Höchbauer, M. Leitner, R. Kern and M. Künle	165
Uniformity Improvement in Carrier Concentration on 150 mm Diameter C-Face Epitaxial Growth of 4H-SiC	
J. Nishio, H. Asamizu, C. Kudou, S. Ito, K. Masumoto, K. Tamura, K. Kojima and T. Ohno	169

Characterization of Comet-Shaped Defects on C-Face 4H-SiC Epitaxial Wafers T. Yamashita, H. Matsuhata, T. Sekiguchi, K. Momose, H. Osawa and M. Kitabatake	173
Influence of Epi-Layer Growth Pits on SiC Device Characteristics C. Kudou, H. Asamizu, K. Tamura, J. Nishio, K. Masumoto, K. Kojima and T. Ohno	177
Low Pressure Homoepitaxial Growth of 4H-SiC on 4°off-Axis Substrates J.C. Hu, Y.M. Zhang, R.X. Jia, Y.H. Wang and B. Xin	181
3C-SiC Crystal on Sapphire by Solution Growth Method K. Shibata, S. Harada and T. Ujihara	185
3C-SiC Polycrystalline Films on Si for Photovoltaic Applications S. Privitera, V. Brancato, D. Spadaro, R. Anzalone, A. Alberti and F. La Via	189
Defect Reduction in Epitaxial 3C-SiC on Si(001) and Si(111) by Deep Substrate Patterning H. von Känel, L. MIGLIO, D. Crippa, T. Kreiliger, M. Mauceri, M. Puglisi, F. Mancarella, R. Anzalone, N. Piluso and F. La Via	193
High Quality 3C-SiC (111) Epitaxial Layer on Si (110) Substrate by Using Si₂Cl₆+C₃H₈ H.T. Lee, H.J. Lee, M.S. Park, Y.S. Jang, W.J. Lee, J.G. Kim and S. Nishino	197
Monte Carlo Study of the early Growth Stages of 3C-SiC on Misoriented <11-20> and <1-100> 6H-SiC Substrates: Role of Step-Island Interaction M. Camarda, A. La Magna and F. La Via	201
Si Surface Preparation for Heteroepitaxial Growth of SiC Using <i>In Situ</i> Oxidation L. Wang, S. Dimitrijević, A. Iacopi, L. Hold, G. Walker, J. Chai and D. Massoubre	205
Understanding of the Growth Mechanism Leading to Twin Boundary Elimination during 3C-SiC Heteroepitaxy on α-SiC Substrate by CVD K. Alassaad, V. Soulière, F. Cauwet, D. Carole, B. Doisneau and G. Ferro	209
PLD Grown 3C-SiC Thin Films on Si: Morphology and Structure S.M. Ryndya, N.I. Kargin, A.S. Gusev and E.P. Pavlova	213
Effect of Nitrogen Dilution in the Optical Properties of Amorphous SiC Thin Films L. Montañez, J.A. Guerra, F. de Zela, A. Winnaker and R. Weingärtner	217

Chapter II: Fundamental and Characterization of SiC

II.1 Fundamental and Material Properties

Temperature Dependence of 4H-SiC Ionization Rates Using Optical Beam Induced Current H. Hamad, C. Raynaud, P. Bevilacqua, S. Scharnholtz and D. Planson	223
Characterising Strain/Stress and Defects in SiC Wafers Using Raman Imaging T. Batten and O. Milikofu	229
Residual Stress Analysis of Indentation on 4H-SiC by Deep-Ultraviolet Excited Raman Spectroscopy T. Kozu, M. Yamaguchi, M. Fujitsuka, O. Milikofu and K. Nishida	233
Comparative Study of n-Type 4H-SiC: Raman vs Photoluminescence Spectroscopy P. Kwasnicki, R. Arvinte, H. Peyre, M. Zielinski and S. Juillaguet	237
Applying Chemometrics for Analysis of SiC Raman Imaging Data O. Milikofu, T. Kozu and T. Batten	241
Probing of Carrier Recombination in n- and p-Type 6H-SiC Using Ultrafast Supercontinuum Pulses P. Grivickas, S. Sampayan, K. Redeckas, M. Vengris and V. Grivickas	245
Optical Characterization of p-Type 4H-SiC Epilayers G. Liaugaudas, D. Dargis, P. Kwasnicki, H. Peyre, R. Arvinte, S. Juillaguet, M. Zielinski and K. Jarašiūnas	249
Photoelectrical Parameters of a PVT Grown Bulk 15R-SiC Crystal at Different Stages of Growth G. Liaugaudas, D. Dargis, K. Jarašiūnas, N. Tsavdaris, E. Sarigiannidou and D. Chaussende	253
Correlations between Crystal Quality and Electrical Properties by Means of Simultaneous Photoluminescence and Photocurrent Analysis S. Privitera, M. Camarda, N. Piluso, R. Anzalone and F. La Via	257
FTIR Studies of Silicon Carbide 1D-Nanostructures I. Karbovnyk, P. Savchyn, A. Huczko, M. Cestelli Guidi, C. Mirri and A.I. Popov	261

Infrared Transmission and Reflectivity Measurements of 4H- and 6H-SiC Single Crystals Y.X. Cui, X.B. Hu and X.G. Xu	265
Two-Dimensional Carrier Profiling on Lightly Doped n-Type 4H-SiC Epitaxially Grown Layers H. ROSSMANN, U. Gysin, A. Bubendorf, T. Glatzel, S.A. Reshanov, A. Schöner, T.A. Jung, E. Meyer and H. Bartolf	269
A Novel Approach to Measuring Doping in SiC by Micro Spot Corona-Kelvin Method D. Marinskiy and A. Savtchouk	273
The Bloch Oscillations and THz Electroluminescence in Natural Superlattices of 6H-, 8H-SiC Polytypes V.I. Sankin, A.V. Andrianov, A.G. Petrov, A.O. Zachar'in, S. Nagalyuk, P.P. Shkrebiy and N.I. Sablina	277
Mechanical Properties and Residual Stress of Thin 3C-SiC(100) Films Determined Using MEMS Structures B. Hähnlein, M. Stubenrauch and J. Pezoldt	281
Observation of Damaged Layers in 4H-SiC Substrates by Mirror Projection Electron Microscope M. Sasaki, K. Tamura, H. Yamaguchi, H. Matsuhata, K. Kojima and M. Kitabatake	285
Features of the Band-Edge Injection Electroluminescence in 4H-SiC pn Structures A.M. Strel'chuk, Y.S. Kuz'michev and K.F. Shtel'makh	289
Conductivity Compensation in CVD-Grown n-4H-SiC under Irradiation with 0.9 MeV Electrons V.V. Kozlovski, A.A. Lebedev, E.V. Bogdanova and N.V. Seredova	293

II.2 Point and Extended Defects

Elimination of Basal Plane Dislocations in Epitaxial 4H-SiC via Multicycle Rapid Thermal Annealing M.J. Tadjer, N.A. Mahadik, B.N. Feigelson, R.E. Stahlbush, E.A. Imhoff, P.B. Klein, J.A. Freitas, J.D. Greenlee and F.J. Kub	297
Basal Plane Dislocation Analysis of 4H-SiC Using Multi Directional STEM Observation T. Sato, Y. Ohtsu, Y. Orai, T. Isshiki and M. Fukui	303
Study on Formation of Dislocation Contrast in 4H-SiC Wafer in Mirror Projection Electron Microscopy Image T. Isshiki and M. Hasegawa	307
Relations between Surface Morphology and Dislocations of SiC Crystal Y. Orai, S. Watanabe, T. Sato, T. Isshiki and M. Fukui	311
Annealing Temperature Dependence of Dislocation Extension and its Effect on Electrical Characteristic of 4H-SiC PIN Diode A. Tanaka, N. Kawabata, M. Tsujimura, Y. Furukawa, T. Hoshino, Y. Ueji, K. Omote, H. Yamaguchi, H. Matsuhata and K. Fukuda	315
Studies of the Origins of Half Loop Arrays and Interfacial Dislocations Observed in Homoepitaxial Layers of 4H-SiC H. Wang, F. Wu, Y. Yang, J.Q. Guo, B. Raghothamachar, T.A. Venkatesh, M. Dudley, J. Zhang, G.Y. Chung, B. Thomas, E. Sanchez, S.G. Mueller, D. Hansen and M.J. Loboda	319
Identification of Stacking Faults by UV Photoluminescence Imaging Spectroscopy on Thick, Lightly-Doped n-Type 4^o-off 4H-SiC Epilayers N. Thierry-Jebali, C. Kawahara, T. Miyazawa, H. Tsuchida and T. Kimoto	323
Photoluminescence Study of Oxidation-Induced Stacking Faults in 4H-SiC Epilayers Y. Miyano, S. Yagi, Y. Hijikata and H. Yaguchi	327
Simple Models for Stacking-Fault Formations in 4H-SiC Epitaxial Layer M. Kitabatake	331
4H-SiC Defects Analysis by Micro Raman Spectroscopy N. Piluso, M. Camarda, R. Anzalone and F. La Via	335
3D Raman Spectroscopy Investigation of Defects in 4H-SiC Epilayer K. Hara, M. Naito, H. Fujibayashi, A. Akiba, Y. Takeuchi, O. Milikofu and T. Kozu	339
Three-Dimensional Imaging of Extended Defects in 4H-SiC by Two-Photon-Excited Band-Edge Photoluminescence R. Tanuma and H. Tsuchida	343

Reduction of Implantation-Induced Point Defects by Germanium Ions in n-Type 4H-SiC T. Sledziewski, G. Ellrott, W. Rösch, H.B. Weber and M. Krieger	347
Isothermal Treatment Effects on the Carbon Vacancy in 4H Silicon Carbide H.M. Ayedh, R. Nipoti, A. Hallén and B.G. Svensson	351
Atomic-Scale Defects in Silicon Carbide for Quantum Sensing Applications V. Dyakonov, H. Kraus, V.A. Soltamov, F. Fuchs, D. Simin, S. Vaeth, A. Sperlich, P. Baranov and G. Astakhov	355
Structural Perfection of Silicon Carbide Crystals Grown on Profiled Seeds by Sublimation Method E. Mokhov, S. Nagalyuk and V.A. Soltamov	359

II.3 Surfaces and Interfaces

<i>Ab Initio</i> Calculations of Absolute Surface Energies of Clean and Hydrogen Covered 3C-SiC(001), (110) and (111) Surfaces S.N. Filimonov	363
Starting Point of Step-Bunching Defects on 4H-SiC Si-Face Substrates K. Tamura, M. Sasaki, C. Kudou, T. Yamashita, H. Sako, H. Asamizu, S. Ito, K. Kojima and M. Kitabatake	367
Surface Orientation Dependence of SiC Oxidation Process Studied by <i>In Situ</i> Spectroscopic Ellipsometry D. Goto, S. Yagi, Y. Hijikata and H. Yaguchi	371
Tuning Optoelectronic Properties of 4H-SiC QDs Using -H, -OH and -F Surface Functionalisation M. Rashid, A.K. Tiwari, N. Wood, P. Briddon, J.P. Goss, M.J. Rayson, N. Wright and A.B. Horsfall	375

Chapter III: Processing of SiC

III.1 Doping, Implantation and Contact

SiC Device Manufacturing: How Processing Impacts the Material and Device Properties U. Grossner, G. Alfieri and R. Nipoti	381
Basal Plane Dislocations Created in 4H-SiC Epitaxy by Implantation and Activation Anneal R.E. Stahlbush, N.A. Mahadik, Q.J. Zhang, A.A. Burk, B.A. Hull and J. Young	387
Estimation of Phosphorus-Implanted 4H-SiC Layer Recrystallization by Electron-Back-Scattering Diffraction Pattern Analysis H. Hanafusa, K. Maruyama, S. Hayashi and S. Higashi	391
Ohmic Contact on n-Type 3C-SiC Activated with SiO₂ Encapsulation F. Li, Y. Sharma, D. Hamilton, C. Fisher, M.R. Jennings, S. Burrows and P.A. Mawby	395
Al⁺ Ion Implanted On-Axis R. Nipoti, A. Parisini, A. Carnera, C. Albonetti, S. Vantaggio and U. Grossner	399
Shallow and Deep Levels in Al⁺-Implanted p-Type 4H-SiC Measured by Thermal Admittance Spectroscopy K. Kawahara, H. Watanabe, N. Miura, S. Nakata and S. Yamakawa	403
Distribution of Secondary Defects and Electrical Activation after Annealing of Al-Implanted SiC Y. Furukawa, H. Suzuki, S. Shimizu, N. Ohse, M. Watanabe and K. Fukuda	407
Process Compatibility of Heavily Nitrogen Doped Layers Formed by Ion Implantation in Silicon Carbide Devices K. Vassilevski, S.K. Roy, N. Wood, A.B. Horsfall and N.G. Wright	411
About the Hole Transport Analysis in Heavy Doped p-Type 4H-SiC(Al) A. Parisini and R. Nipoti	416
Silicon Nitride Encapsulation to Preserve Ohmic Contacts Characteristics in High Temperature, Oxygen Rich Environments S.K. Roy, K. Vassilevski, N.G. Wright and A.B. Horsfall	420
Preliminary Study on the Effect of Micrometric Ge-Droplets on the Characteristics of Ni/4H-SiC Schottky Contacts M. Vivona, F. Giannazzo, K. Alassaad, V. Soulière, G. Ferro and F. Roccaforte	424

Evolution of the Electrical and Structural Properties of Ti/Al/W Contacts to p-Type Implanted 4H-SiC upon Thermal Annealing	
M. Vivona, G. Greco, R. Lo Nigro, S. Di Franco, F. Giannazzo, S. Rascunà, M. Saggio and F. Roccaforte	428
A Study on the Chemistry of Epitaxial Ti₃SiC₂ Formation on 4H-SiC Using Al-Ti Annealing	
T. Abi-Tannous, M. Soueidan, G. Ferro, M. Lazar, B. Toury, M.F. Beaufort, J.F. Barbot, J. Penuelas and D. Planson	432
Electrical Characterization of Ni-Silicide Schottky Contacts on SiC for High Performance Temperature Sensor	
R. Pascu, G. Pristavu, G. Brezeanu, F. Draghici, M. Badila, I. Rusu and F. Craciunoiu	436
Sputtered Ohmic Cobalt Silicide Contacts to 4H-SiC	
K. Smedfors, C. Zetterling and M. Östling	440
Investigation of Ti/Ni Bilayer Contacts to n-Type 4H-SiC	
V.K. Sundaramoorthy, Y.L. Song and R.A. Minamisawa	444
Extremely Enhanced Diffusion of Nitrogen in 4H-SiC Observed in Liquid-Nitrogen Immersion Irradiation of Excimer Laser	
A. Ikeda, D. Marui, H. Ikenoue and T. Asano	448
Investigation of Pressure Dependent Thermal Contact Resistance between Silver Metallized SiC Chip and DBC Substrate	
Z. Toth Pal, Y.F. Zhang, I. Belov, H.P. Nee and M. Bakowski	452

III.2 Dielectric Growth and Characterization

Influence of Conduction-Type on Thermal Oxidation Rate in SiC(0001) with Various Doping Densities	
T. Kobayashi, J. Suda and T. Kimoto	456
Characterization of Inhomogeneity in SiO₂ Films on 4H-SiC Epitaxial Substrate by a Combination of Fourier Transform Infrared Spectroscopy and Cathodoluminescence Spectroscopy	
M. Yoshikawa, H. Seki, K. Inoue, T. Kobayashi and T. Kimoto	460
Fabrication of 3C-SiC MOS Capacitors Using High-Temperature Oxidation	
Y.K. Sharma, F. Li, C.A. Fisher, M.R. Jennings, D. Hamilton, S.M. Thomas, A. Pérez-Tomás and P.A. Mawby	464
Direct Observation of Dielectric Breakdown at Step-Bunching on 4H-SiC	
Y. Mori, M. Matsumura, H. Hamamura, T. Mine, A. Shima, R. Yamada and Y. Shimamoto	468
Evaluation of F-N Tunneling Emission Current in MOS Capacitor Fabricated on Step Bunching	
K. Yamada, O. Ishiyama, H. Sako, J. Senzaki and M. Kitabatake	472
Influence of Annealing, Oxidation and Doping on Conduction-Band near Interface Traps in 4H-SiC Characterized by Low Temperature Conductance Measurements	
S. Noll, M. Rambach, M. Grieb, D. Scholten, A.J. Bauer and L. Frey	476
Inversion-Channel MOS Devices for Characterization of 4H-SiC/SiO₂ Interfaces	
A.I. Mikhaylov, A.V. Afanasyev, V.V. Luchinin, S.A. Reshanov, A. Schöner, L. Knoll, R.A. Minamisawa, G. Alfieri and H. Bartolf	480
Improving Interface Quality of 4H-SiC MOS Devices with High Temperature Oxidation Process in Mass Produce Furnace	
H.Y. Xu, Q. Yang, X.L. Wang, X.Y. Liu, Y.L. Zhao, C. Li and H. Watanabe	484
Tailoring the Interface between Dielectric and 4H-SiC by Ion Implantation	
S.S. Suvanam, D.M. Martin, C. Zetterling and A. Hallén	488
Influence of Phosphorous Auto-Doping on the Characteristics of SiO₂/SiC Gate Dielectrics	
M.H. Weng, A.E. Murphy, C. Ryan, B.J.D. Furnival, D.A. Smith, D.T. Clark, R.A.R. Young, E.P. Ramsay, R.F. Thompson and A.B. Horsfall	492
Influence of Phosphorus Implantation on Electrical Properties of Al/SiO₂/4H-SiC MOS Structure	
K. Krol, M. Sochacki, M. Turek, J. Żuk, P. Borowicz, D. Teklińska, P. Konarski, M. Miśnik, A. Domanowska, A. Michalewicz and J. Szmidt	496
Characteristics of MOS Capacitors with NO and POCl₃ Annealed Gate Oxides on (0001), (11-20) and (000-1) 4H-SiC	
S. Chowdhury, K. Yamamoto, C.W. Hitchcock and T.P. Chow	500

Plasma Nitridation of 4H-SiC by Glow Discharge of N₂/H₂ Mixed Gases Y. Akahane, K. Kimura, T. Kano, Y. Watanabe, T. Yamakami, S. Fujimaki and K. Kamimura	504
Passivation of 4H-SiC/SiO₂ Interface Traps by Oxidation of a Thin Silicon Nitride Layer A.I. Mikhaylov, A.V. Afanasyev, V.V. Luchinin, S.A. Reshanov, A. Schöner, L. Knoll, R.A. Minamisawa, G. Alfieri and H. Bartolf	508
MOS Interface Characteristics of <i>In Situ</i> Ge-Doped 4H-SiC Homoepitaxial Layers A. Salinaro, K. Alassaad, D. Peters, P. Friedrichs and G. Ferro	512
An Investigation of Capacitance-Voltage Hysteresis in Al₂O₃/SiC MIS Capacitors Y.Y. Wang, X.L. Wang, C.Z. Li, J. Wu, L.C. Han, H.J. Shen, W.W. Wang and X.Y. Liu	516

III.3 Etching and Machining

Comparison of Different Novel Chip Separation Methods for 4H-SiC K.O. Dohnke, K. Kaspar and D. Lewke	520
High-Speed Dicing of SiC Wafers by Femtosecond Pulsed Laser A. Nakajima, Y. Tateishi, H. Murakami, H. Takahashi, M. Ota, R. Kosugi, T. Mitani, S.I. Nishizawa and H. Ohashi	524
Thermal Laser Separation – A Novel Dicing Technology Fulfilling the Demands of Volume Manufacturing of 4H-SiC Devices D. Lewke, K.O. Dohnke, H.U. Zühlke, M. Cerezuela Barreto, M. Schellenberger, A.J. Bauer and H. Rysse	528
Elimination of Microtrenching in Trenches in 4H-Silicon Carbide Using Shadow Masking Z. Mohammadi, V.A. Shah, M.R. Jennings, C.A. Fisher and P.A. Mawby	533
Planarization of 6-Inch 4H-SiC Wafer Using Catalyst-Referred Etching A. Isohashi, Y. Sano, T. Kato and K. Yamauchi	537
Removal of Mechanical-Polishing-Induced Surface Damages on 4H-SiC by Chemical Etching and its Effect on Subsequent Epitaxial Growth Y.Z. Yao, Y. Ishikawa, Y. Sugawara and K. Sato	541
Effect of Surface Damage on SiC Wafer Shape K. Moeggenborg, T. Kegg, C. Parfeniuk, T. Stoney and J. Quast	545
Planarization of Epitaxial SiC Trench Structures by Plasma Ion Etching A.Z. Zhang, S.A. Reshanov, A. Schöner, W. Kaplan, N. Kwietniewski, J.K. Lim and M. Bakowski	549
Chlorine Trifluoride Gas Transport and Etching Rate Distribution in Silicon Carbide Dry Etcher D. Yajima, K. Nakagomi, H. Habuka and T. Kato	553

Chapter IV: SiC Devices and Circuits

IV.1 Diodes

Low Frequency Noise in 4H-SiC Schottky Diodes Under Forward Bias E.I. Shabunina, M.E. Levinshtein, N.M. Shmidt, P.A. Ivanov, J.W. Palmour and L. Cheng	559
Impact of Stacking Fault on the I-V Characteristics of 4H-SiC Schottky Barrier Diode H.J. Jung, S.B. Yun, I.H. Kang, J.H. Moon, W.J. Kim and W. Bahng	563
Improvement of I-V Characteristics of Schottky Barrier Diode by 4H-SiC Surface Planarization H. Fujiwara, A. Onogi, T. Katsuno, T. Morino, T. Endo and Y. Sano	567
Si_{1-x}C_x/Si(001) Heterostructures for Use in Schottky Diode Rectifiers Demonstrating High Breakdown Voltage and Negligible Leakage Current G. Colston, M. Myronov, S. Rhead, V.A. Shah, Y. Sharma, P.A. Mawby and D. Leadley	571
Ion-Induced Anomalous Charge Collection Mechanisms in SiC Schottky Barrier Diodes T. Makino, M. Deki, S. Onoda, N. Hoshino, H. Tsuchida and T. Ohshima	575
Fabrication and Application of 1.7KV SiC-Schottky Diodes G. Chen, S. Bai, A. Liu, L. Wang, R.H. Huang, Y.H. Tao and Y. Li	579
Cryogenic to High Temperature Exploration of 4H-SiC W-SBD M. Berthou, B. Asllani, P. Brosselard and P. Godignon	583

A Study of Post Annealing Effects in the Repair of High Resistance Failures with Unstable Schottky Barrier Height in 4H-SiC Schottky Barrier Diode S.S. Kyoung, E.S. Jung, T.Y. Kang, C.H. Yang and M.Y. Sung	588
Static and Dynamic Characteristics of SiC MOSFETs and SBDs for 3.3 kV 400 A Full SiC Modules K. Wada, H. Tamaso, S. Itoh, K. Kanbara, T. Hiyoshi, S. Toyoshima, J. Genba, H. Tokuda, T. Sugimura, H. Michikoshi, T. Tsuno and Y. Mikamura	592
Influence of Trench Structure on Reverse Characteristics of 4H-SiC JBS Diodes K. Konishi, N. Kameshiro, N. Yokoyama, A. Shima and Y. Shimamoto	596
Temperature-Dependent Characteristics of 4H-SiC Buried Grid JBS Diodes J.K. Lim, S.A. Reshanov, W. Kaplan, A. Zhang, T. Hjort, A. Schöner, M. Bakowski and H.P. Nee	600
Comparison of the Planar-JBS against the Trench-MOS Rectifier-Design Based on 4H-SiC for 3.3 kV Applications H. Bartolf	604
A New 1200V SiC MPS Diode with Improved Performance and Ruggedness M. Draghici, R. Rupp, R. Gerlach and B. Zippelius	608
The Effect of Proton and Carbon Irradiation on 4H-SiC 1700V MPS Diode Characteristics P. Hazdra, R.K. Sharma and S. Popelka	612
Thermal Simulation of Paralleled SiC PiN Diodes in a Module Designed for 6.5 kV/1 kA C.F. Bayer, E. Bär, B. Kallinger and P. Berwian	616
Ion Implanted Lateral p⁺-i-n⁺ Diodes on HPSI 4H-SiC R. Nipoti, F. Moscatelli, A. Roncaglia, F. Bonafe, F. Mancarella, P. de Nicola, A. Nath and M.V. Rao	620
Simulations of a Lateral PiN Diode on Si/SiC Substrate for High Temperature Applications C.W. Chan, P.M. Gammon, V.A. Shah, H. Chen, M.R. Jennings, C.A. Fisher, A. Pérez-Tomás, M. Myronov and P.A. Mawby	624
Analytical Prediction of the Cross-Over Point in the Temperature Coefficient of the Forward Characteristics of 4H-SiC p⁺-i-n Diodes L. di Benedetto, G.D. Licciardo, S. Bellone and R. Nipoti	628
Temperature Dependence of Minority Carrier Lifetime in Epitaxially Grown p⁺-p⁻-n⁺ 4H-SiC Drift Step Recovery Diodes A.V. Afanasyev, B.V. Ivanov, V.A. Ilyin, A.F. Kardo-Sysoev, V.V. Luchinin, S.A. Reshanov, A. Schöner and A.A. Smirnov	632
4H-Silicon Carbide p-n Diode for High Temperature (600 °C) Environment Applications S.Q. Shao, W.C. Lien, A. Maralani, J.C. Cheng, K.L. Dorsey and A.P. Pisano	636
Observation and Analysis of a Non-Uniform Avalanche Phenomenon in 4H-SiC 4°-Off (0001) p-n Diodes Terminated with a Floating-Field Ring K. Mochizuki, H. Okino, H. Matsushima and Y. Toyota	640
4H-SiC P⁺N UV Photodiodes for Space Applications B. Berenguier, L. Ottaviani, S. Biondo, M. Lazar, F. Milesi, O. Palais, F. Torregrosa, A. Lyoussi, E.V. Kalinina and A. Lebedev	644
Characterization of 4H-SiC pn Structures with Unstable Excess Current A.M. Strel'chuk, E.B. Yakimov, A.A. Lavrent'ev, E.V. Kalinina and A.A. Lebedev	648
The Impact of Interface Charge on the Breakdown Voltage of Terminated 4H-SiC Power Devices H. Matsushima, H. Okino, K. Mochizuki and R. Yamada	652
Robust Double-Ring Junction Termination Extension Design for High Voltage Power Semiconductor Devices Based on 4H-SiC A. Hürner, L. di Benedetto, T. Erlbacher, H. Mitlehner, A.J. Bauer and L. Frey	656

IV.2 Field Effect Transistor

Industrial Approach for Next Generation of Power Devices Based on 4H-SiC M. Saggio, A. Guarnera, E. Zanetti, S. Rascunà, A. Frazzetto, D. Salinas, F. Giannazzo, P. Fiorenza and F. Roccaforte	660
Proton and Electron Irradiation in Oxynitrided Gate 4H-SiC MOSFET: A Recent Open Issue M. Florentin, M. Alexandru, A. Constant, P. Michel, J. Montserrat, J. Millan and P. Godignon	667

Instability of Critical Electric Field in Gate Oxide Film of Heavy Ion Irradiated SiC MOSFETs	
M. Deki, T. Makino, K. Kojima, T. Tomita and T. Ohshima	673
Bias-Temperature-Stress Response of Commercially-Available SiC Power MOSFETs	
R. Green, A. Lelis, M. El and D.B. Habersat	677
Degradation and Reliability of Bare Dies Operated up to 300°C	
D. Hamilton, M. Jennings, S. York, S.A. Hindmarsh, Y. Sharma, C. Fisher and P. Mawby	681
Exact Characterization of Threshold Voltage Instability in 4H-SiC MOSFETs by Non-Relaxation Method	
M. Sometani, D. Okamoto, S. Harada, H. Ishimori, S. Takasu, T. Hatakeyama, M. Takei, Y. Yonezawa, K. Fukuda and H. Okumura	685
SiC MOSFETs in Hard-Switching Bidirectional DC/DC Converters	
T. Heckel, B. Eckardt, M. März and L. Frey	689
Channel Mobility Improvement in 4H-SiC MOSFETs Using a Combination of Surface Counter-Doping and NO Annealing	
A.C. Ahyi, A. Modic, C. Jiao, Y. Zheng, G. Liu, L.C. Feldman and S. Dhar	693
Simulating the Influence of Mobile Ionic Oxide Charge on SiC MOS Bias-Temperature Instability Measurements	
D.B. Habersat, N. Goldsman and A. Lelis	697
Next-Generation Planar SiC MOSFETs from 900 V to 15 kV	
S. Allen, V. Pala, E. VanBrunt, B. Hull, L. Cheng, S. Ryu, J. Richmond, M. O'Loughlin, A.A. Burk and J. Palmour	701
Recovery of the Electrical Characteristics of SiC MOSFETs Irradiated with Gamma-Rays by Thermal Treatments	
T. Yokoseki, H. Abe, T. Makino, S. Onoda, Y. Tanaka, M. Kandori, T. Yoshie, Y. Hijikata and T. Ohshima	705
Impact of Nitric Oxide Post Oxidation Anneal on the Bias Temperature Instability and the On-Resistance of 4H-SiC nMOSFETs	
G. Rescher, G. Pobegen and T. Aichinger	709
Study of Mobility Limiting Mechanisms in (11-20) 4H-SiC NO Annealed MOSFETs	
K. Yamamoto, S. Chowdhury and T.P. Chow	713
Study of Geometrical Effects in Charge Pumping Current for Lateral SiC nMOSFETs Electrical Characterization	
M. Florentin, J.M. Rafi, F. Chevalier, V. Soler, L. Konczewicz, S. Contreras, S. Juillaguet, J. Montserrat and P. Godignon	717
Comparative Study of Characteristics of Lateral MOSFETs Fabricated on 4H-SiC (11-20) and (1-100) Faces	
K. Ariyoshi, S. Harada, J. Senzaki, T. Kojima, Y. Kobayashi, Y. Tanaka, R. Iijima and T. Shinohe	721
Reliable 4H-SiC MOSFET with High Threshold Voltage by Al₂O₃-Inserted Gate Insulator	
A. Shima, K. Watanabe, T. Mine, N. Tega, H. Hamamura and Y. Shimamoto	725
Effect of Fixed Oxide Charges and Donor-Like Interface Traps on the Breakdown Voltage of SiC Devices with FGR and JTE Terminations	
C.T. Yen, H.T. Hung, C.C. Hung, C.Y. Lee, L.S. Lee, Y.F. Huang, T.M. Yang and C.Y. Cheng	729
Electrical Characterization of 3C-SiC Lateral MOSFETs Fabricated on Heteroepitaxial Films Including High Density of Defects	
Y. Watanabe, N. Kawana, T. Horikawa and K. Kamimura	733
Effect of Bulk Potential Engineering on the Transport Properties of SiC MOSFETs: Characterization and Interpretation	
V. Uhnevionak, A. Burenkov, C. Strenger, G. Ortiz, V. Mortet, E. Bedel-Pereira, F. Cristiano, A.J. Bauer and P. Pichler	737
Gate Oxide Reliability of 4H-SiC V-Groove Trench MOSFET with Thick Bottom Oxide	
T. Hiyoshi, T. Masuda, Y. Saito, K. Wada, T. Tsuno and Y. Mikamura	741
Characterization of Interface State Density from Subthreshold Slope of MOSFETs at Low Temperatures (≥ 10 K)	
H. Yoshioka, J. Senzaki, A. Shimoizato, Y. Tanaka and H. Okumura	745
High-Mobility SiC MOSFETs with Chemically Modified Interfaces	
D.J. Lichtenwalner, L. Cheng, S. Dhar, A.K. Agarwal, S. Allen and J.W. Palmour	749

Impact of Post-Trench Processing on the Electrical Characteristics of 4H-SiC Trench-MOS Structures with Thick Top and Bottom Oxides	
C.T. Banzhaf, M. Grieb, M. Rambach, A.J. Bauer and L. Frey	753
Improved Evaluation Method for Channel Mobility in SiC Trench MOSFETs	
K. Kutsuki, S. Kawaji, Y. Watanabe, S. Miyahara and J. Saito	757
Introduction of Depletion Stopper for Reduction of JFET Resistance for 4H-SiC Trench MOSFET	
Y. Kagawa, R. Tanaka, N. Fujiwara, K. Sugawara, Y. Fukui, N. Miura, M. Imaizumi, S. Nakata and S. Yamakawa	761
CIMOSFET: A New MOSFET on SiC with a Superior $R_{on} \cdot Q_{gd}$ Figure of Merit	
Q.C.J. Zhang, J. Duc, B. Hull, J. Young, S.H. Ryu, S. Allen and J.W. Palmour	765
Low R_{ons} in 3kV 4H-SiC UMOSFET with MeV Implanted Buried P-Base Region	
S. Harada, M. Kato, M. Shinozaki, Y. Kobayashi, K. Ariyoshi, T. Kojima, M. Sometani, J. Senzaki, Y. Tanaka and H. Okumura	769
Electrical Properties Evaluation on High Quality Hetero-Epitaxial 3C-SiC(001) for MOSFET Applications	
R. Anzalone, S. Privitera, A. Alberti, N. Piluso, P. Fiorenza and F. La Via	773
Cryogenic Characterization of Commercial SiC Power MOSFETs	
H. Chen, P.M. Gammon, V.A. Shah, C.A. Fisher, C.W. Chan, S. Jahdi, D.P. Hamilton, M.R. Jennings, M. Myronov, D.R. Leadley and P.A. Mawby	777
Electrical Characterization of a 4H-SiC JFET Wafer: DC Parameter Variations for Extreme Temperature IC Design	
P.G. Neudeck, L.Y. Chen, D.J. Spry, G.M. Beheim and C.W. Chang	781
The Influence of Neutron Irradiation on Electrical Characteristics of 4H-SiC Power Devices	
P. Hazdra, S. Popelka and V. Zahlava	785
VLS Grown 4H-SiC Buried P^+ Layers for JFET Lateral Structures	
S. Sejlil, F. Laariedh, M. Lazar, D. Carole, C. Brylinski, D. Planson, G. Ferro, C. Raynaud and H. Morel	789
4H-SiC VJFETs with Self-Aligned Contacts	
K. Zekentes, A. Stavrinidis, G. Konstantinidis, M. Kayambaki, K. Vamvoukakis, E. Vassakis, K. Vasilevskiy, A.B. Horsfall, N.G. Wright, P. Brosselard, S.Q. Niu, M. Lazar, D. Planson, D. Tournier, N. Camara and M. Bucher	793
Bulk Thickness and Short Circuit Capacity of a 1200V 4H-SiC VJFET	
S. Niu, M. Berthou and D. Tournier	797
IR Lock-In Thermography Analysis to Evidence Dynamic Mis-Behavior of SiC Device Prototypes	
F. Chevalier, J. Leon, X. Perpiña, D. Tournier, X. Jordá, J. Montserrat and P. Godignon	801
Temperature Dependent Characterization of Bipolar Injection Field-Effect-Transistors (BiFET) for Determining the Short-Circuit-Capability	
A. Hürner, T. Erlbacher, H. Mitlehner, A.J. Bauer and L. Frey	806

IV.3 Other Devices

Short-Circuit Capability Exploration of Silicon Carbide Devices	
M. Berthou, D. Planson and D. Tournier	810
Characterization and Comparison of 1.2kV SiC Power Devices from Cryogenic to High Temperature	
T. Chailloux, C. Calvez, D. Tournier and D. Planson	814
Improvement of Current Gain and Breakdown Voltage in 4H-SiC BJTs Employing High-k Dielectric as an Interfacial Layer	
L. Yuan, Y.M. Zhang, Q.W. Song, X.Y. Tang and Y.M. Zhang	818
Improvement of the Current Gain Stability of SiC Junction Transistors	
S.G. Sundaresan, B. Grummel, D. Hamilton and R. Singh	822
Dynamic Voltage Rise Control (DVRC) Applied to SiC Bipolar Junction Transistors	
C. Bödeker, S. Rugen and N. Kaminski	826
Development of a PSPICE Model for 1200 V/800 A SiC Bipolar Junction Transistor Power Module	
D. Johannesson and M. Nawaz	830

Investigation of the Breakdown Voltage in High Voltage 4H-SiC BJT with Respect to Oxide and Interface Charges	
A. Salemi, H. Elahipanah, C. Zetterling and M. Östling	834
4.5-kV 20-mΩ.cm² Implantation-Free 4H-SiC BJT with Trench Structures on the Junction Termination Extension	
H. Elahipanah, A. Salemi, C. Zetterling and M. Östling	838
Device Performance and Switching Characteristics of 16 kV Ultrahigh-Voltage SiC Flip-Type n-Channel IE-IGBTs	
Y. Yonezawa, T. Mizushima, K. Takenaka, H. Fujisawa, T. Deguchi, T. Kato, S. Harada, Y. Tanaka, D. Okamoto, M. Sometani, M. Okamoto, M. Yoshikawa, T. Tsutsumi, Y. Sakai, N. Kumagai, S. Matsunaga, M. Takei, M. Arai, T. Hatakeyama, K. Takao, T. Shinohe, T. Izumi, T. Hayashi, K. Nakayama, K. Asano, M. Miyajima, H. Kimura, A. Otsuki, K. Fukuda, H. Okumura and T. Kimoto	842
27 kV, 20 A 4H-SiC n-IGBTs	
E. van Brunt, L. Cheng, M.J. O'Loughlin, J. Richmond, V. Pala, J.W. Palmour, C.W. Tipton and C. Scozzie	847
Growth and Characterization of Thick Multi-Layer 4H-SiC Epiwafer for Very High-Voltage p-Channel IGBTs	
T. Miyazawa, K. Nakayama, A. Tanaka, K. Asano, S. Ji, K. Kojima, Y. Ishida and H. Tsuchida	851
Silicon Carbide Nanowire Devices for Label-Free Electrical DNA Detection	
L. Fradetal, E. Bano, L. Montes, G. Atolini and V. Stambouli	855
High Temperature CMOS Circuits on Silicon Carbide	
E. Ramsay, J. Breeze, D.T. Clark, A. Murphy, D. Smith, R. Thompson, S. Wright, R. Young and A. Horsfall	859
Simulations of Interactions between Fast Neutrons and 4H-SiC Detectors	
S. Biondo, W. Vervisch, L. Ottaviani, V. Vervisch, R. Ferrone and A. Lioussy	863
SiC UV Detectors under Heavy Ions Irradiation	
E.V. Kalinina, A.A. Lebedev, B. Berenguier, L. Ottaviani and V.A. Skuratov	867
High Voltage Wide Bandgap Photoconductive Switching	
S.E. Sampayan, M. Bora, C. Brooksby, G.J. Caporaso, A. Conway, S. Hawkins, B. Hickman, C. Holmes, H. Nguyen, R. Nikolic, D. Palmer, L. Voss, L. Wang and A. Waters	871
Study of the Stability of 4H-SiC Detectors by Thermal Neutron Irradiation	
F. Issa, L. Ottaviani, V. Vervisch, D. Szalkai, L. Vermeeren, A. Lyoussi, A. Kuznetsov, M. Lazar, A. Klix, O. Palais, R. Ferone and A. Hallén	875
Development of SiC Power Module and Loss Evaluation in DC-DC Converter Circuit Application	
T. Funaki, S. Yamamoto, S. Harada, Y. Iizuka, K. Fukuda, A. Sugiki, T. Hiratani, H. Kimura and T. Saitou	879
Full SiC DCDC-Converter with a Power Density of more than 100kW/dm³	
O. Kreutzer, M. März and H. Nakata	884
Comparison of Turn-Off Strategies for SiC Thyristors	
S.G. Sundaresan and R. Singh	889
High Current (1225A) Optical Triggering of 18-kV 4H-SiC Thyristor in Purely Inductive Load Circuit	
S. Rumyantsev, M. Levinshtein, T. Saxena, M. Shur, L. Cheng and J. Palmour	893
Design and Characterization of 500 °C Schmitt Trigger in 4H-SiC	
S. Kargarrazi, L. Lanni and C. Zetterling	897
Hetero-Epitaxial Single Crystal 3C-SiC Opto-Mechanical Pressure Sensor	
A. Roncaglia, R. Anzalone, L. Belsito, F. Mancarella, M. Camarda, N. Piluso, R. Nipoti and F. La Via	902
Improved Planar MOS Barrier Schottky (PMBS) Rectifier with High-<i>k</i> Dielectrics	
Q.W. Song, Y.M. Zhang, X.Y. Tang, Y.H. Wang, H. Yuan and Y.M. Zhang	906
ECL-Based SiC Logic Circuits for Extreme Temperatures	
L. Lanni, B.G. Malm, M. Östling and C. Zetterling	910
High-Temperature Operation of Electrostatically-Excited Single-Crystalline 4H-SiC Microcantilever Resonators	
K. Sato, K. Adachi, H. Okamoto, H. Yamaguchi, T. Kimoto and J. Suda	914
Pressureless Ag Thin-Film Die-Attach for SiC Devices	
C. Oh, S. Nagao, T. Sugahara and K. Suganuma	919

Nanoscale Dynamic Mechanical Analysis on Heat-Resistant Silsesquioxane Nanocomposite for Power-Device Packaging S. Nagao, N. Fujisawa, T. Sugioka, S. Ogawa, T. Fujibayashi, T. Wada, T. Sugahara and K. Suganuma	923
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Chapter V: Related Materials

V.1 Other Carbon Based Materials

Electrical Properties of Hydrogen Intercalated Epitaxial Graphene/SiC Interface Investigated by Nanoscale Current Mapping F. Giannazzo, S. Hertel, A. Albert, G. Fisichella, A. La Magna, F. Roccaforte, M. Krieger and H.B. Weber	929
Graphene Ohmic Contacts to n-Type Silicon Carbide (0001) S. Hertel, A. Finkler, M. Krieger and H.B. Weber	933
Electrical Characterization of Epitaxial Graphene Field-Effect Transistors with High-k Al₂O₃ Gate Dielectric Fabricated on SiC Substrates T. Hopf, K. Vassilevski, E. Escobedo-Cousin, P. King, N.G. Wright, A.G. O'Neill, A.B. Horsfall, J. Goss, G. Wells and M. Hunt	937
Realization and Characterization of Graphene on 4H-SiC for Tera-Hertz Transistors J. Pezard, J. Lhuillier, Z. El-Friach, V. Soulière, B. Vilquin, P. Rojo Romeo and M. Lazar	941
RHEED Study of Epitaxial Graphene on Conductive and Semi-Insulating 6H-SiC (0001) Substrates I.S. Kotousova, S.P. Lebedev and A.A. Lebedev	945
A Study on Graphitization of 4H-SiC(0001) Surface under Low Pressure Oxygen Atmosphere and Effects of Pre-Oxidation Treatment Y. Nagahisa, Y. Tsuchiya and E. Tokumitsu	949
Tuning the Terrace and Step Stability of 6H-SiC (0001) for Graphene Film Deposition G. Rius, N. Mestres, O. Eryu and P. Godignon	953
Raman Spectra and Strain Uniformity of Epitaxial Graphene Grown on SiC(0001) Y.F. Hu, H. Guo, Y.M. Zhang and Y.M. Zhang	957
On the Formation of Graphene by Ge Intercalation of a 4H-SiC Surface N. Chandran, M. Sall, J. Arvanitidis, D. Christofilos, K. Alassaad, G. Ferro, V. Soulière and E.K. Polychroniadis	961
Si NWs Conversion to Si-SiC Core-Shell NWs by MBE F. Lloret, D. Araujo, M.P. Villar, L. Liu and K. Zekentes	965
The Role of Aluminium in the Synthesis of Mesoporous 4H Silicon Carbide J. Hvam, P. Morgen, T.E. Warner, E.M. Skou and T. Wolff	970
Synthesis and Characterization of Al₄SiC₄: A “New” Wide Band Gap Semiconductor Material D. Zevgitis, O. Chaix-Pluchery, B. Doisneau, M. Modreanu, J. La Manna, E. Sarigiannidou and D. Chaussende	974
Silicon Growth on 3C-SiC(001)/Si(001): Pressure Influence and Thermal Effect R. Khazaka, M. Portail, P. Vennéguès, M. Zielinski, T. Chassagne, D. Alquier and J.F. Michaud	978
Influence of Diamond CVD Growth Conditions and Interlayer Material on Diamond/GaN Interface T. Izak, O. Babchenko, V. Jirásek, G. Vanko, M. Vojs and A. Kromka	982
Electrical Properties of Graphene Contacts to AlGaIn/GaN Heterostructures G. Fisichella, G. Greco, F. Roccaforte and F. Giannazzo	986

V.2 Nitrides and other Materials

Chemical Vapor Deposition of Boron Nitride Thin Films on SiC M. Chubarov, H. Pedersen, H. Högberg, M. Garbrecht, Z. Czigány, S.G. Andersson and A. Henry	990
Innovations in SiC Backside Processing and Manufacturing for GaN/SiC Products Y.H. Wang, C.H. Chen, Y.W. Chang, S.H. Huang, Y.F. Wei, M.H. Weng, J.H. Du, W.C. Wang, I.T. Cho and W. Wohlmuth	995
Microstructure and Temperature Dependent Electrical Characteristics of Ohmic Contacts to AlGaIn/GaN Heterostructures G. Greco, F. Iucolano and F. Roccaforte	999

Structural Investigation of Si Quantum Dots Grown by CVD on AlN/Si(111) and 3C-SiC/Si(100) Epilayers	
R. Dagher, R. Khazaka, S. Vézian, M. Teissiere, A. Michon, M. Zielinski, T. Chassagne, Y. Cordier and M. Portail	1003
Effect of Various Crucibles for High Quality AlN Crystal Growth on SiC Seed by PVT Method	
H.J. Lee, H.T. Lee, H.W. Shin, M.S. Park, Y.S. Jang, W.J. Lee, D.Y. Kim, S.K. Hong and J.G. Kim	1007
Synchrotron X-Ray Study on Crack Prevention in AlN Crystals Grown on Gradually Decomposing SiC Substrates	
T.S. Argunova, M.Y. Gutkin, O.P. Kazarova, E.N. Mokhov, S. Nagalyuk and J.H. Je	1011
Novel Poly-Si/GaN Vertical Heterojunction Diode	
K. Emori, T. Marui, Y. Saito, W. Ni, Y. Nakajima, T. Hayashi and M. Hoshi	1015